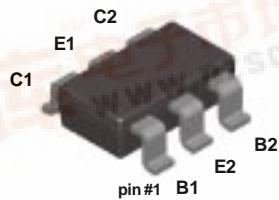




Discrete POWER & Signal Technologies

FMBA06



SuperSOT™-6
Mark: .1G

NPN Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 33.

Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FMBA06	
P _D	Total Device Dissipation Derate above 25°C	700	mW
		5.6	mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient	180	°C/W



NPN Multi-Chip General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage*	$I_C = 1.0\text{ mA}, I_B = 0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\ \mu\text{A}, I_C = 0$	4.0			V
I_{CEO}	Collector-Cutoff Current	$V_{CE} = 60\text{ V}, I_B = 0$			0.1	μA
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 80\text{ V}, I_E = 0$			0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	100			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$			0.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$			1.2	V

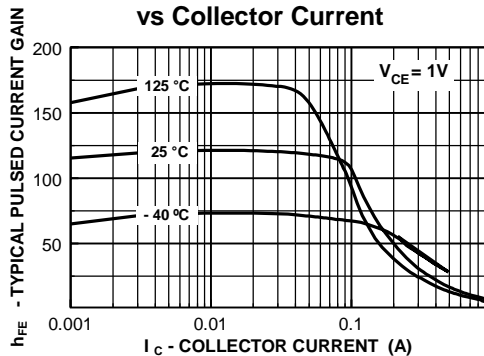
SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10\text{ mA}, V_{CE} = 2.0\text{ V},$ $f = 100\text{ MHz}$		150		MHz
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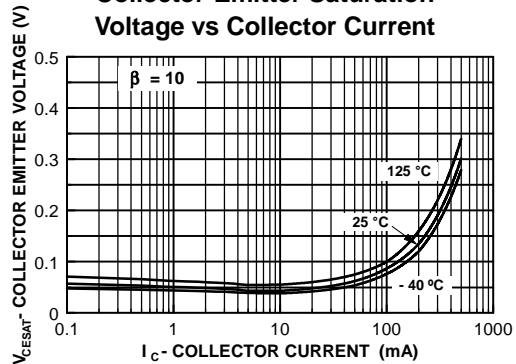
*Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current



Collector-Emitter Saturation Voltage vs Collector Current



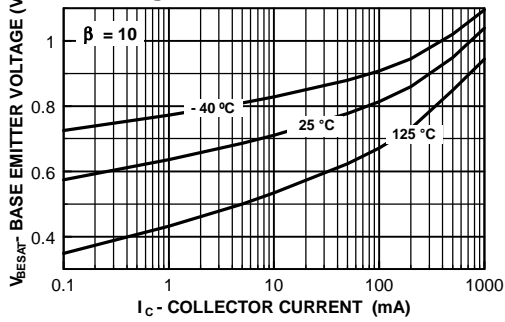
NPN Multi-Chip General Purpose Amplifier

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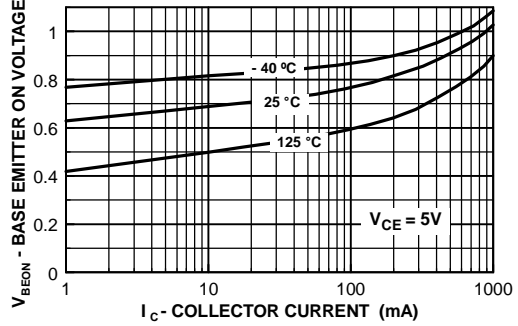
FMBA06

Typical Characteristics (continued)

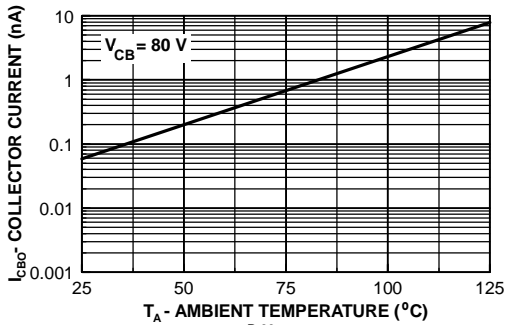
Base-Emitter Saturation Voltage vs Collector Current



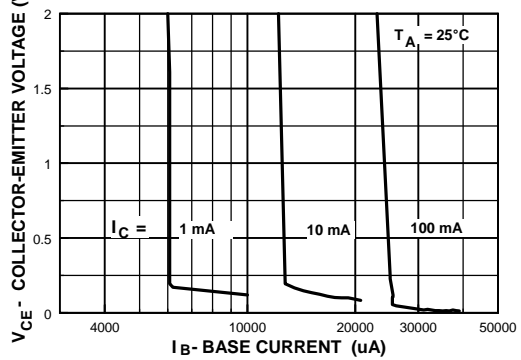
Base Emitter ON Voltage vs Collector Current



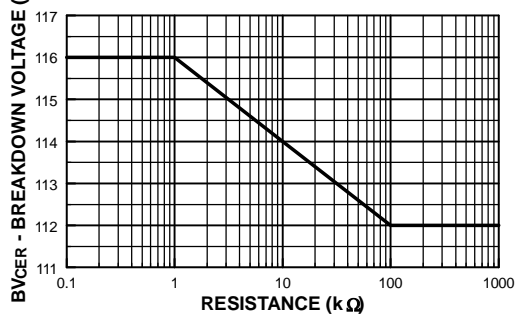
Collector-Cutoff Current vs. Ambient Temperature



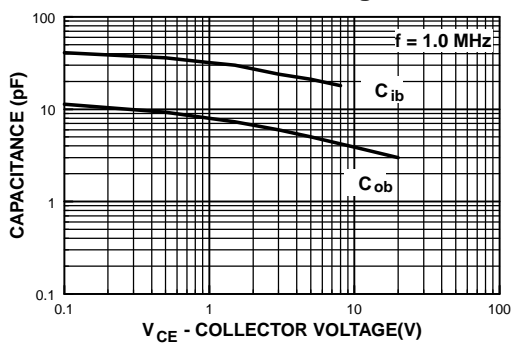
Collector Saturation Region



Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



Input and Output Capacitance vs Reverse Voltage



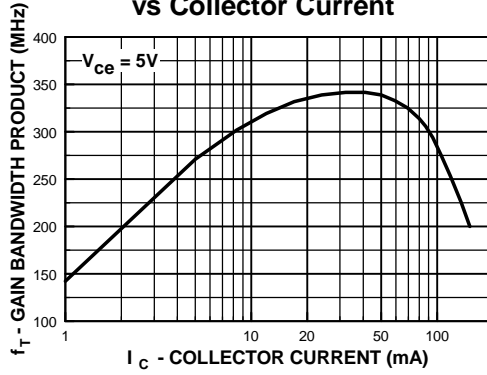
NPN Multi-Chip General Purpose Amplifier

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Typical Characteristics (continued)

Gain Bandwidth Product vs Collector Current



Power Dissipation vs Ambient Temperature

